



Complementary 30-V (D-S) MOSFET

PRODUCT SUMMARY						
	V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
P-Channel	- 30	0.051 at V _{GS} = - 10 V	- 6.4			
		0.075 at V _{GS} = - 6 V	- 5.3			
N-Channel	30	0.035 at V _{GS} = 10 V	7.7			
		0.050 at V _{GS} = 4.5 V	6.5			

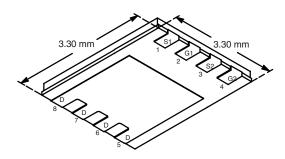
FEATURES

- · Halogen-free Option Available
- TrenchFET® Power MOSFET
- New Low Thermal Resistance
- PowerPAK[®] Package with Low 1.07 mm Profile



RoHS

PowerPAK 1212-8



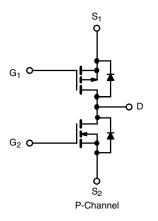
Bottom View

Ordering Information: Si7501DN-T1-E3 (Lead (Pb)-free)

Si7501DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

- · Backlight Inverter
- DC/DC Converter
 - 4 Cell Battery



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter		Symbol	P-Channel		N-Channel		
			10 s	Steady State	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	- 30		30		V
Gate-Source Voltage		V_{GS}	± 25		± 20		v
Continuous Prain Current /T 150 °C\8	T _A = 25 °C	I _D	- 6.4	- 4.5	7.7	5.4	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 5.1	- 3.6	4.7	4.3	
Pulsed Drain Current		I _{DM}	- 25		25		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.6	- 1.3	2.6	1.3	
Mariana Barra Biraira Kana	T _A = 25 °C	- P _D	3.1	1.6	3.1	1.6	W
Maximum Power Dissipation ^a	T _A = 70 °C		3	1.0	2	1.0	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150				- °C
Soldering Recommendations (Peak Temperature) ^{b, c}			260				

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 s	- R _{thJA}	32	40		
	Steady State		65	81	°C/W	
Maximum Junction-to-Foot (Case)	Steady State	R _{thJC}	5	6.3		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.



SPECIFICATIONS $T_J = 25 ^{\circ}C$, unless otherwise noted									
Parameter	Symbol	Test Conditions		Min.	Тур.	Max.	Unit		
Static			ı		Т		1		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$ P-Cl		- 1.0		- 3	V		
		$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	N-Ch	1.0		3			
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 25 \text{ V}$	P-Ch			± 200	nA		
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	N-Ch			± 100			
Zava Cata Valtaga Dvain Cuwant	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V	P-Ch			- 1			
		V _{DS} = 30 V, V _{GS} = 0 V	N-Ch			1	μΑ		
Zero Gate Voltage Drain Current		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	P-Ch			- 5			
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			5			
	I _{D(on)}	$V_{DS} \ge -5 \text{ V}, V_{GS} = -10 \text{ V}$	P-Ch	- 25			—		
On-State Drain Current ^a		$V_{DS} \le 5 \text{ V}, V_{GS} = 10 \text{ V}$	N-Ch 25				Α		
		V _{GS} = - 10 V, I _D = - 6.4 A	P-Ch		0.041	0.051	Ω		
	R _{DS(on)}	V _{GS} = 10 V, I _D = 7.7 A	N-Ch		0.028	0.035			
Drain-Source On-State Resistance ^a		V _{GS} = - 6 V, I _D = - 5.3 A	P-Ch		0.055	0.075			
		V _{GS} = 4.5 V, I _D = 6.5 A	N-Ch		0.040	0.050			
	9 _{fs}	V _{DS} = - 15 V, I _D = - 6.4 A	P-Ch		13		S		
Forward Transconductance ^a		V _{DS} = 15 V, I _D = 7.7 A	N-Ch		15				
	V _{SD}	I _S = - 1.7 A, V _{GS} = 0 V	P-Ch		- 0.80	- 1.2			
Diode Forward Voltage ^a		I _S = 1.7 A, V _{GS} = 0 V	N-Ch		0.80	1.2	V		
Dynamic ^b			ı		I.		1		
Total Cata Chausa	_		P-Ch		12.5	19			
Total Gate Charge	Q_g	P-Channel	N-Ch		9	14	nC		
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -6.4 \text{ A}$	P-Ch		2.5				
date doubte offarge		N-Channel	N-Ch		2				
Gate-Drain Charge	Q _{gd}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 7.7 \text{ A}$	P-Ch		3.6				
			N-Ch		1.3				
Gate Resistance	R _g		P-Ch		9		Ω		
			N-Ch P-Ch		3 10	15	<u> </u>		
Turn-On Delay Time	t _{d(on)}	P-Channel	N-Ch		10	15			
		$V_{DD} = -15 \text{ V}, R_{L} = 5 \Omega$	P-Ch		20	30			
Rise Time	t _r	$I_D \cong -3 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 1 \Omega$	N-Ch		15	25			
	t _{d(off)}	- N-Channel	P-Ch		25	40	1		
Turn-Off Delay Time		$V_{DD} = 15 \text{ V}, R_1 = 5 \Omega$	N-Ch		20	30	ns		
Fall Time	t _f	$I_D \cong 3 \text{ A, } V_{GEN} = 10 \text{ V, } R_G = 1 \Omega$	P-Ch		30	45			
Fall Time			N-Ch		10	15			
Source-Drain Reverse Possyory Time	ime t _{rr}	I _F = - 1.7 A, dl/dt = 100 A/μs	P-Ch		25	50			
Source-Drain Reverse Recovery Time		I _F = 1.7 A, dI/dt = 100 A/μs	N-Ch		20	40			

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

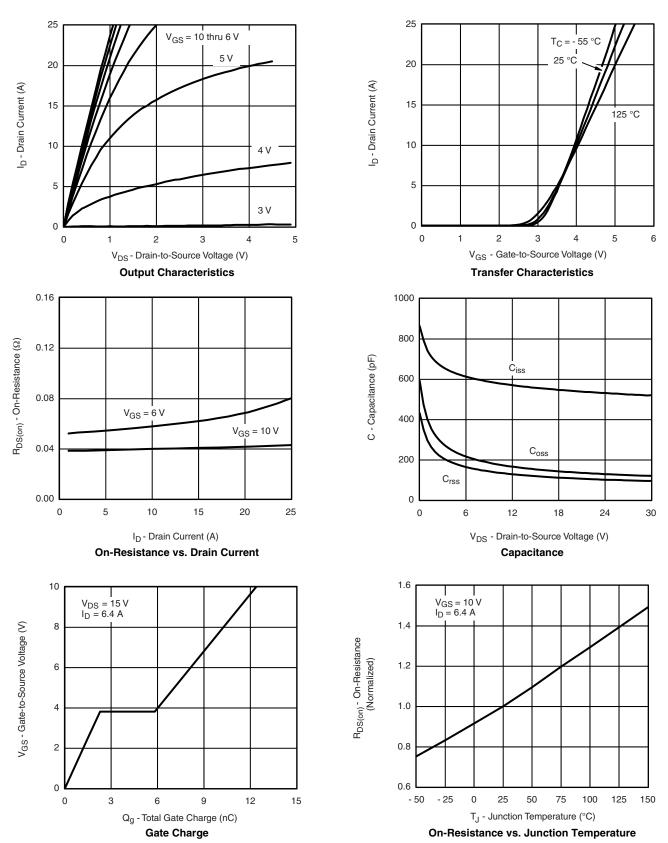
b. Guaranteed by design, not subject to production testing.





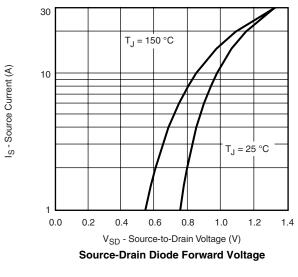


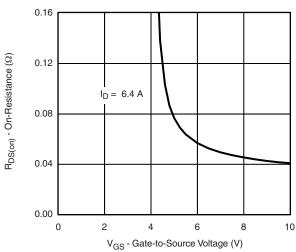
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

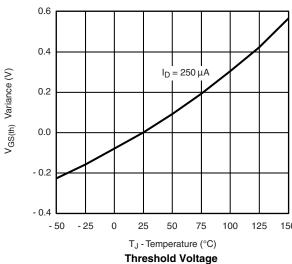


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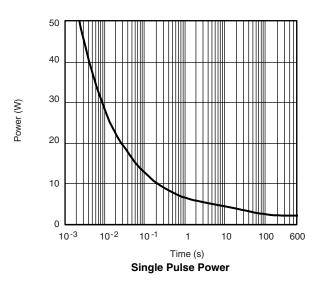
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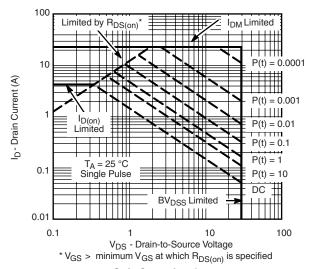








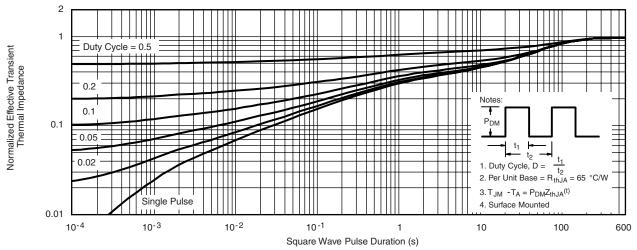




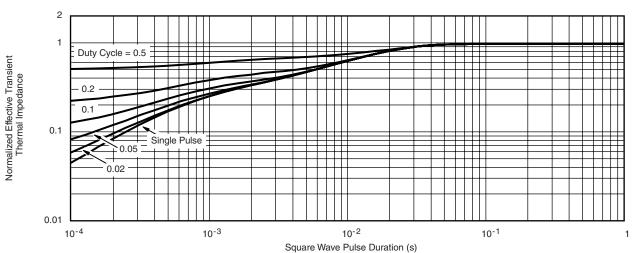
Safe Operating Area



P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



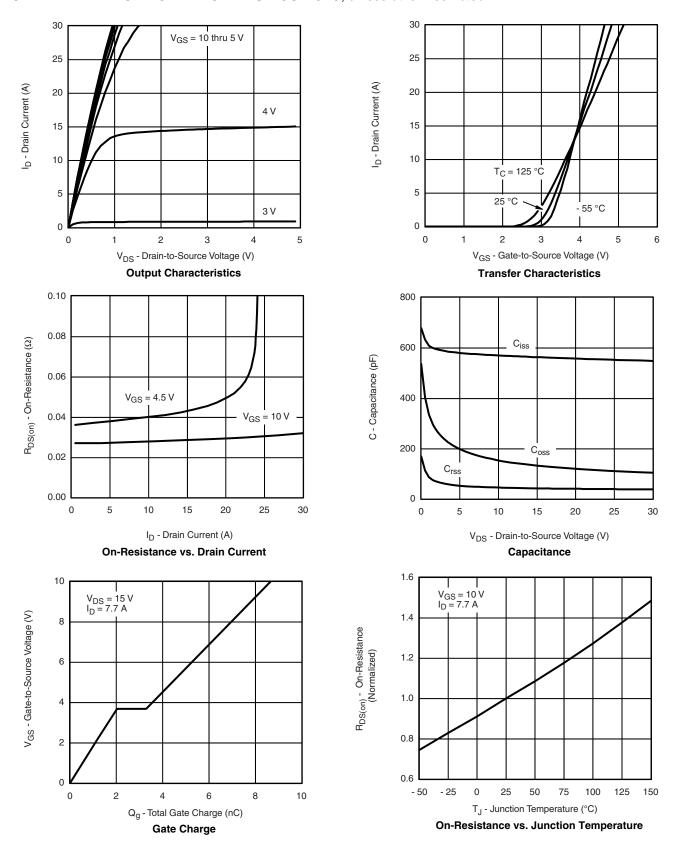
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



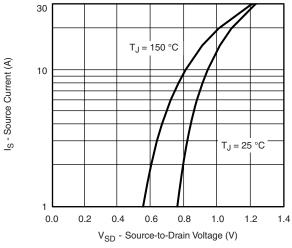
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

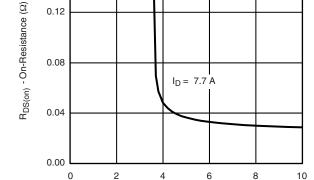






N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



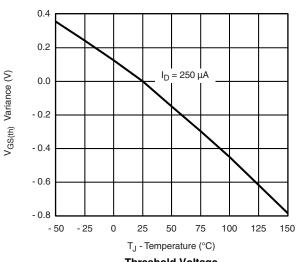


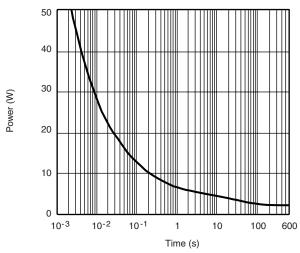
0.16

0.12

Source-Drain Diode Forward Voltage

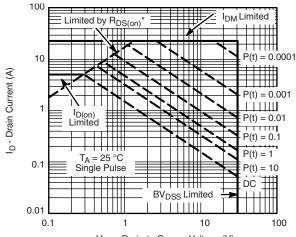






Threshold Voltage

Single Pulse Power

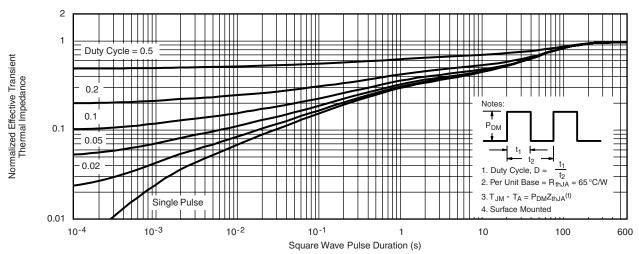


 $V_{\mbox{\footnotesize DS}}$ - Drain-to-Source Voltage (V) * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

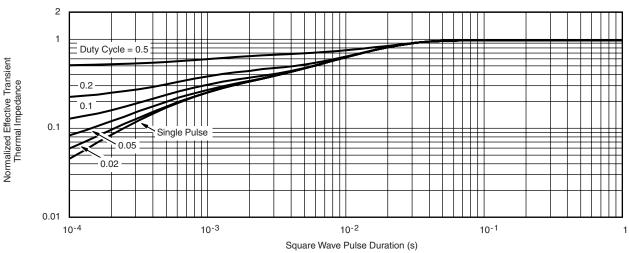
Safe Operating Area



N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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